

BRGB75P65AHA

Rev.A Jan.-2026

描述 / Descriptions

TO-247 塑封封装绝缘栅双极晶体管。

Insulated-Gate Bipolar Transistor in a TO-247 Plastic Package.

特征 / Features

650V , 75A

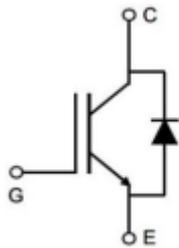
$V_{CE(SAT)} = 1.90V(\text{typ.}) @ V_{GE} = 15V, I_C = 75A$

用途 / Applications

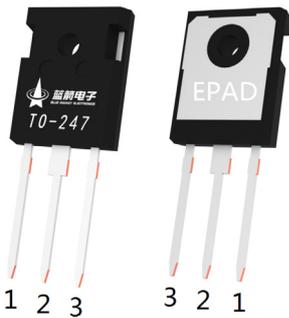
太阳能转换器、不间断电源、焊接转换器、中高范围开关频率转换器。

Solar Converters, Uninterrupted Power Supply, Welding Converters, Mid to High Range Switching Frequency Converters.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2、EPAD : C

PIN 3 : E

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings($T_a=25^{\circ}\text{C}$)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit	
Collector-Emitter Voltage	V_{CES}	650	V	
Gate-Emitter Voltage	V_{GES}	± 30	V	
Continuous Collector Current	I_C	$T_C=25^{\circ}\text{C}$	150	A
		$T_C=100^{\circ}\text{C}$	75	A
Pulsed Collector Current , Limited by T_{Jmax}	I_{CM}	300	A	
Continuous Diode Forward Current	I_F	$T_C=25^{\circ}\text{C}$	160	A
		$T_C=100^{\circ}\text{C}$	80	A
Power Dissipation	P_D	$T_C=25^{\circ}\text{C}$	750	W
		$T_C=100^{\circ}\text{C}$	375	W
Operating Junction Temperature Range	T_J	-40 to +175	$^{\circ}\text{C}$	
Storage Temperature Range	T_{STG}	-55 to +150	$^{\circ}\text{C}$	
Maximum Junction-to-Ambient	$R_{\theta JA}$	80	$^{\circ}\text{C}/\text{W}$	
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	0.20	$^{\circ}\text{C}/\text{W}$	
Maximum Diode Junction-to-Case	$R_{\theta JC}$	0.55	$^{\circ}\text{C}/\text{W}$	

电性能参数 / Electrical Characteristics($T_c=25^{\circ}\text{C}$)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector-Emitter Breakdown Voltage	BV_{CES}	$I_C=250\mu\text{A}$, $V_{GE}=0\text{V}$	650			V
Zero Gate Voltage Collector current	I_{CES}	$V_{CE}=650\text{V}$, $V_{GE}=0\text{V}$			250	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE}=0\text{V}$, $V_{GE}=\pm 30\text{V}$			± 100	nA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE}=V_{GE}$, $I_C=250\mu\text{A}$	4.0	5.0	5.5	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE}=15\text{V}$, $I_C=75\text{A}$	$T_J=25^{\circ}\text{C}$	1.90	2.20	V
			$T_J=125^{\circ}\text{C}$		2.00	
Total Gate Charge	Q_g	$V_{GE}=15\text{V}$, $V_{CE}=480\text{V}$ $I_C=75\text{A}$		200		nC
Gate to Emitter Charge	Q_{ge}			20		
Gate to Collector Charge	Q_{gc}				32	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Turn-On Delay Time	$t_{d(on)}$	V _{GE} =15V, V _{CC} =400V I _C =75A, R _G =10Ω Inductive Load	TC=25°C		38		ns
			Tc=150°C		36		ns
Turn-On Rise Time	t_r		TC=25°C		118		ns
			Tc=150°C		100		ns
Turn-Off Delay Time	$t_{d(off)}$		TC=25°C		267		ns
			Tc=150°C		300		ns
Turn-Off Fall Time	t_f		TC=25°C		81		ns
			Tc=150°C		85		ns
Turn-On Energy	E _{on}		TC=25°C		4.65		mJ
			Tc=150°C		4.50		mJ
Turn-Off Energy	E _{off}		TC=25°C		2.45		mJ
			Tc=150°C		2.70		mJ
Total Switching Energy	E _{ts}	TC=25°C		7.10		mJ	
		Tc=150°C		7.20		mJ	
Input Capacitance	C _{ies}	V _{GE} =0V, f=1MHz	V _{CE} =25V		2850		pF
Output Capacitance	C _{oes}				410		pF
Reverse Transfer Capacitance	C _{res}				185		pF
Diode Forward Voltage	V _F	I _F =75A	T _J =25°C		1.50		V
			T _J =125°C		1.35		
Diode Reverse Recovery Time	T _{rr}	VR=400V, I _F =75A dI _F /dt=500 A/us	Tc=25°C		80		ns
			Tc=150°C		125		ns
Diode Reverse Recovery Charge	Q _{rr}		Tc=25°C		0.58		μC
			Tc=150°C		1.25		μC
Diode Peak Reverse Recovery Current	I _{rm}		Tc=25°C		12.5		A
			Tc=150°C		18.5		A

电参数曲线图 / Electrical Characteristic Curve

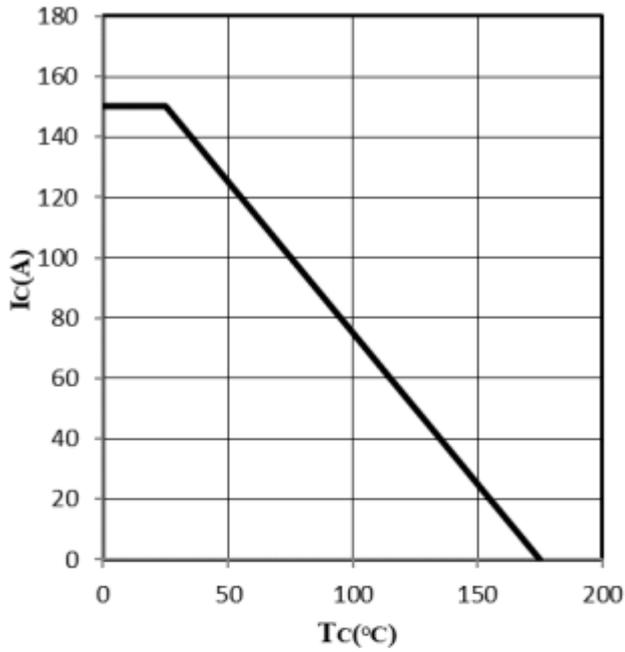


Fig 1. DC Collector current as a function of case temperature ($V_{GE} \geq 15V$, $T_j \leq 150^\circ C$)

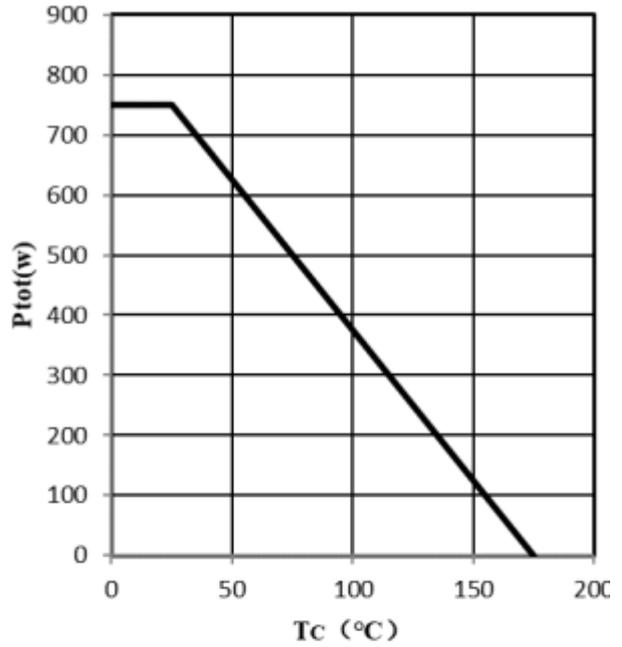


Fig 2. Power dissipation as a function of case temperature ($T_j \leq 150^\circ C$)

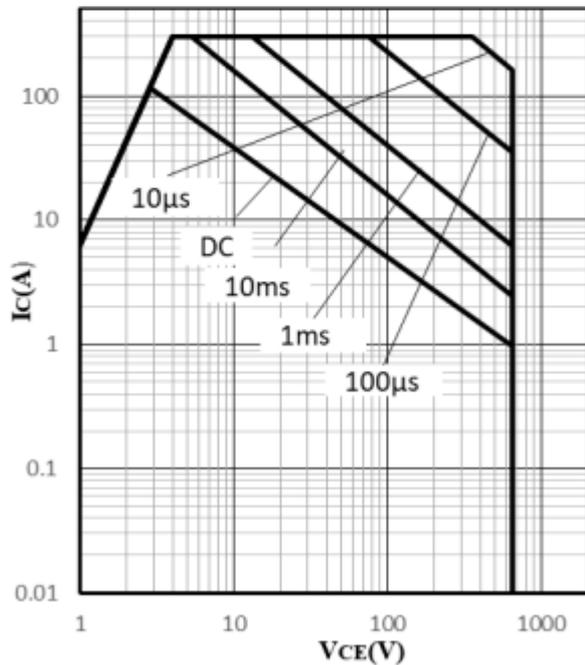


Fig 3. IGBT Forward safe operation area

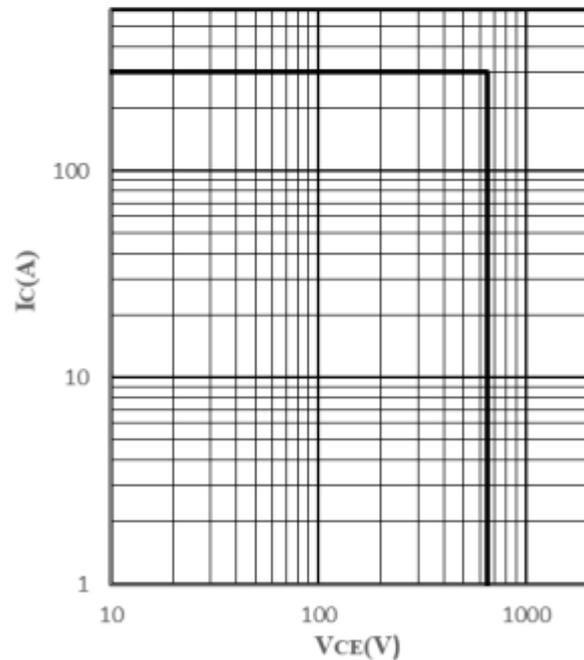


Fig 4. IGBT Reverse safe operation area

电参数曲线图 / Electrical Characteristic Curve

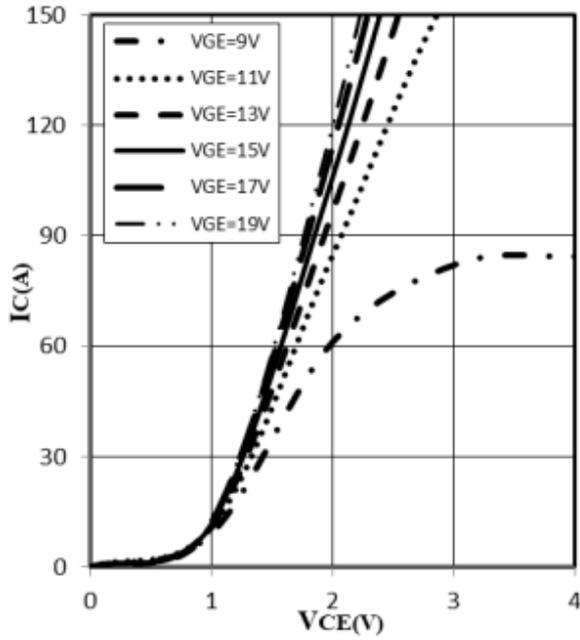


Fig 5. Typical output characteristic ($T_j=25^\circ\text{C}$)

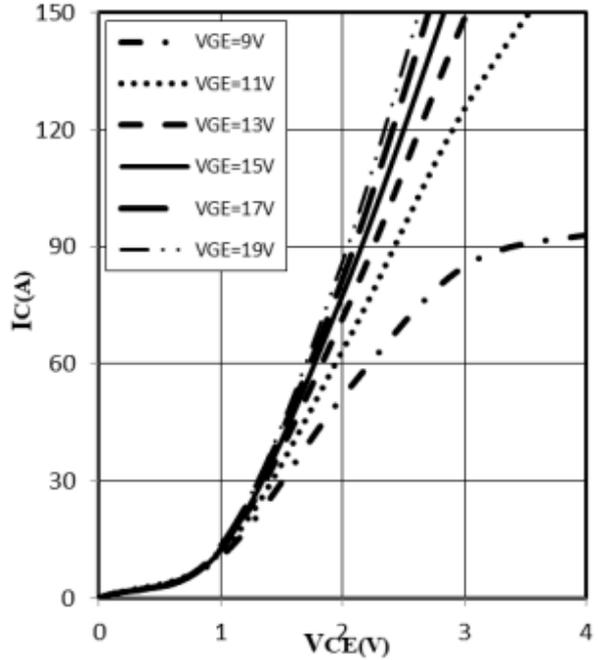


Fig 6. Typical output characteristic ($T_j=125^\circ\text{C}$)

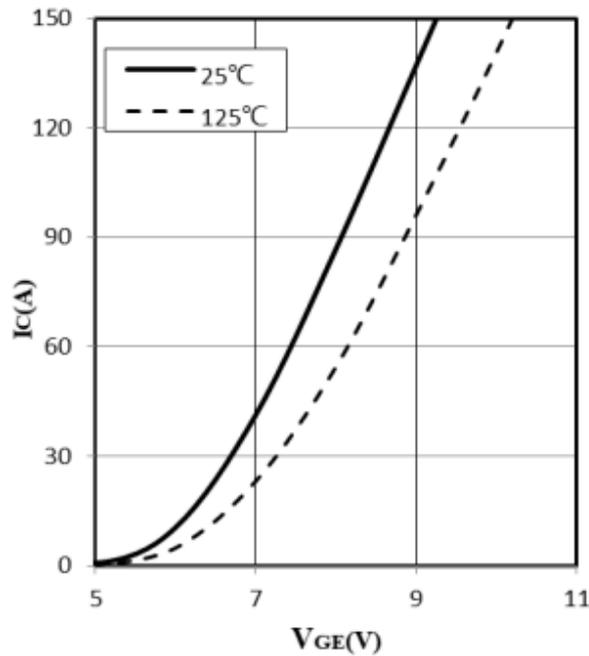


Fig 7. Typical transfer characteristic ($V_{CE}=20\text{V}$)

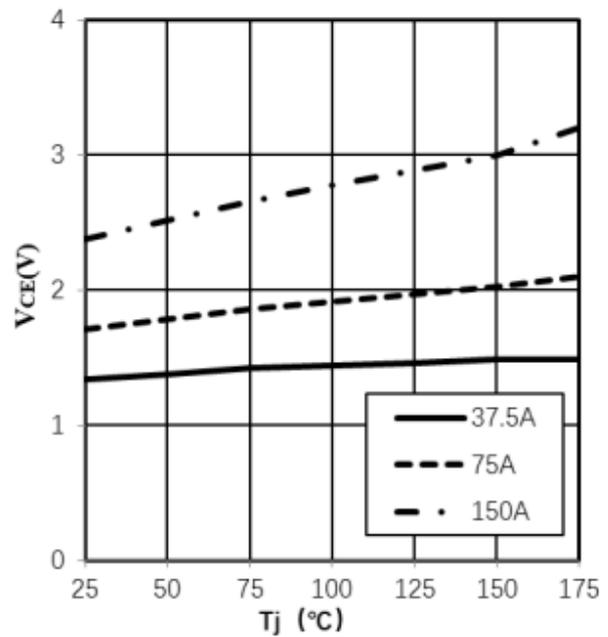


Fig 8. Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15\text{V}$)

电参数曲线图 / Electrical Characteristic Curve

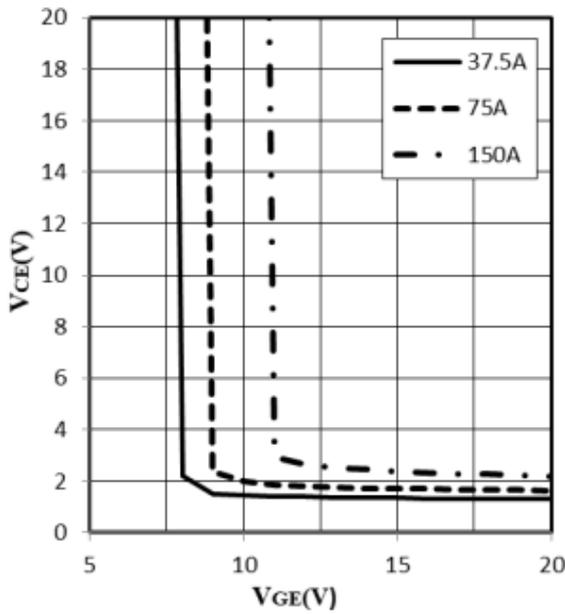


Fig 9. Typical collector-emitter saturation voltage as a function of V_{GE} ($T_j=25^\circ\text{C}$)

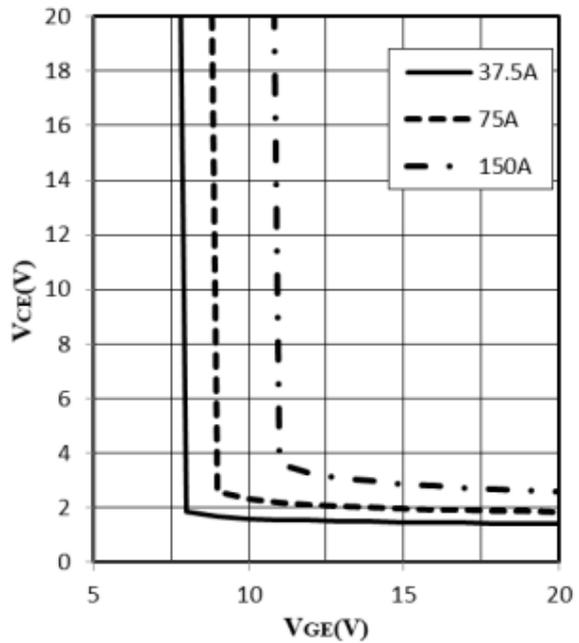


Fig 10. Typical collector-emitter saturation voltage as a function of V_{GE} ($T_j=125^\circ\text{C}$)

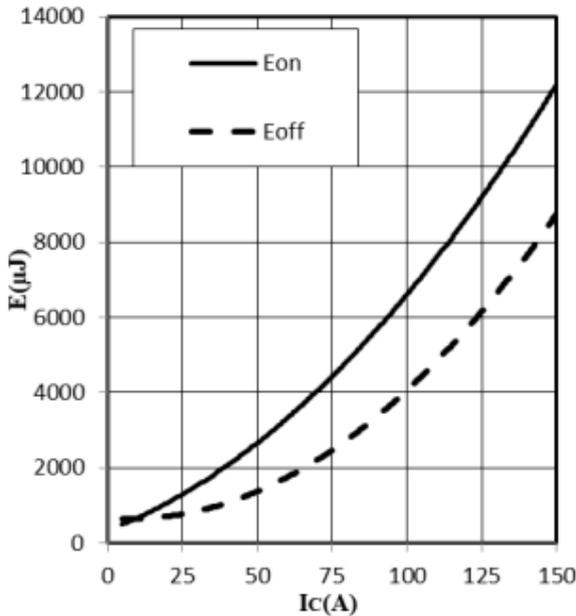


Fig 11. Typical switch energy as a function of I_c (inductive load, $T_j=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $R_G=10\Omega$)

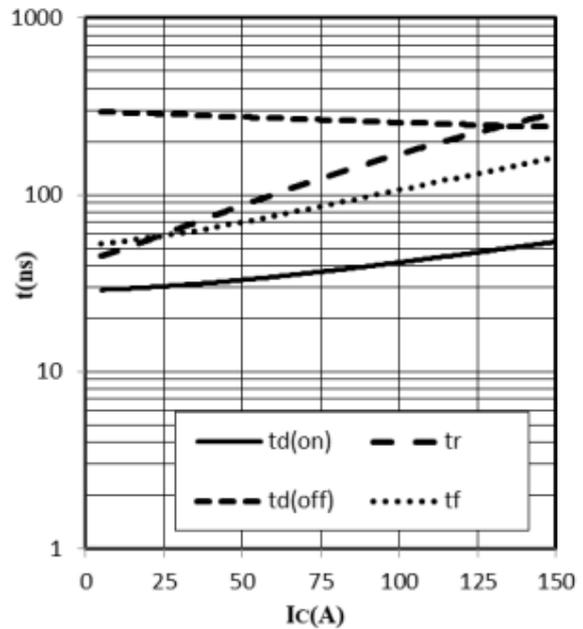


Fig 12. Typical switch time as a function of I_c (inductive load, $T_j=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $R_G=10\Omega$)

电参数曲线图 / Electrical Characteristic Curve

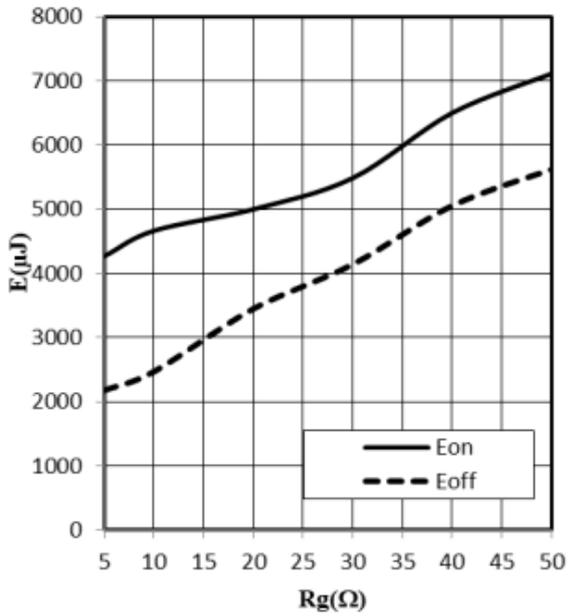


Fig 13. Typical switch energy as a function of R_G
(inductive load, $T_j=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_c=75\text{A}$)

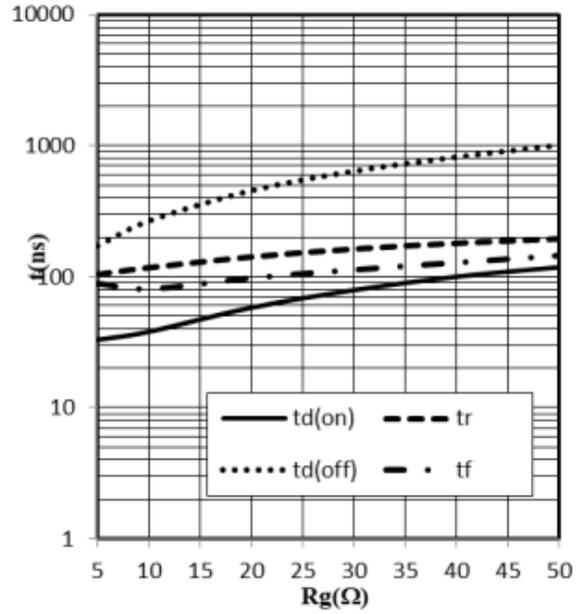


Fig 14. Typical switch time as a function of R_G
(inductive load, $T_j=25^\circ\text{C}$, $V_{CE}=400\text{V}$, $V_{GE}=15\text{V}$, $I_c=75\text{A}$)

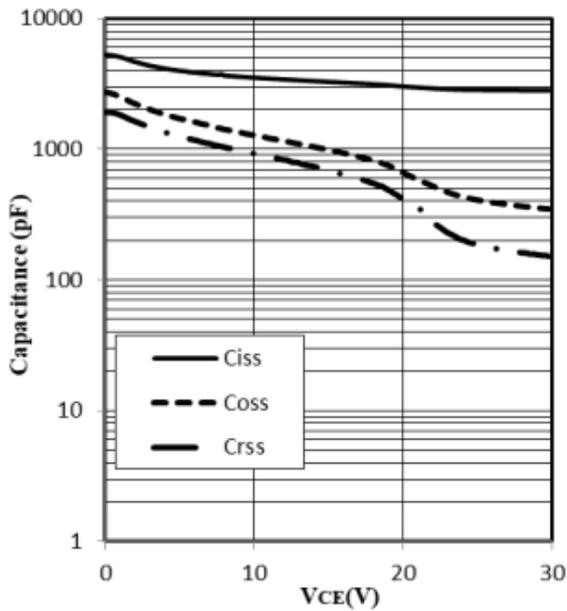


Fig 15. Typical capacitance as a function of collector-emitter voltage ($V_{GE}=0\text{V}$, $f=1\text{MHz}$)

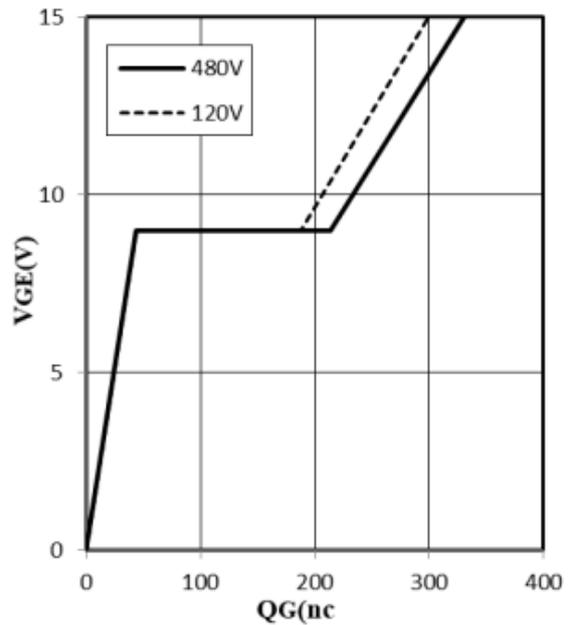


Fig 16. Typical gate charge ($I_c=75\text{A}$)

电参数曲线图 / Electrical Characteristic Curve

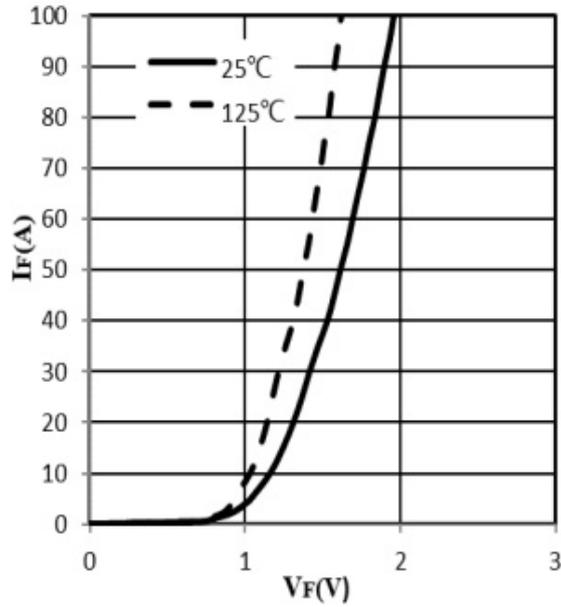


Fig 17. Typical diode forward current as a function of forward voltage

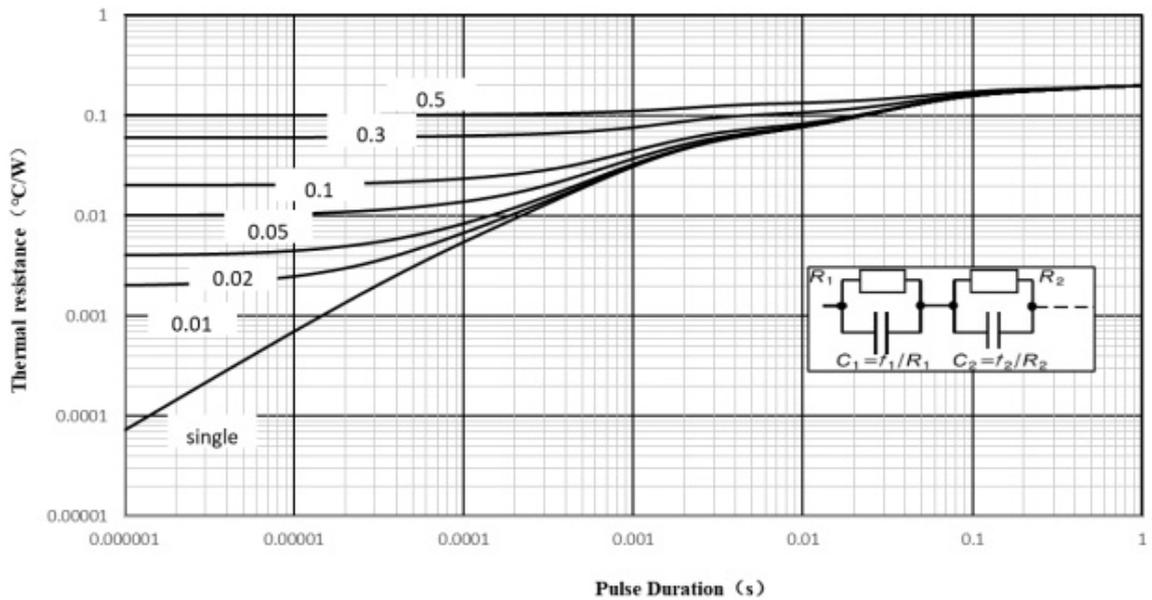
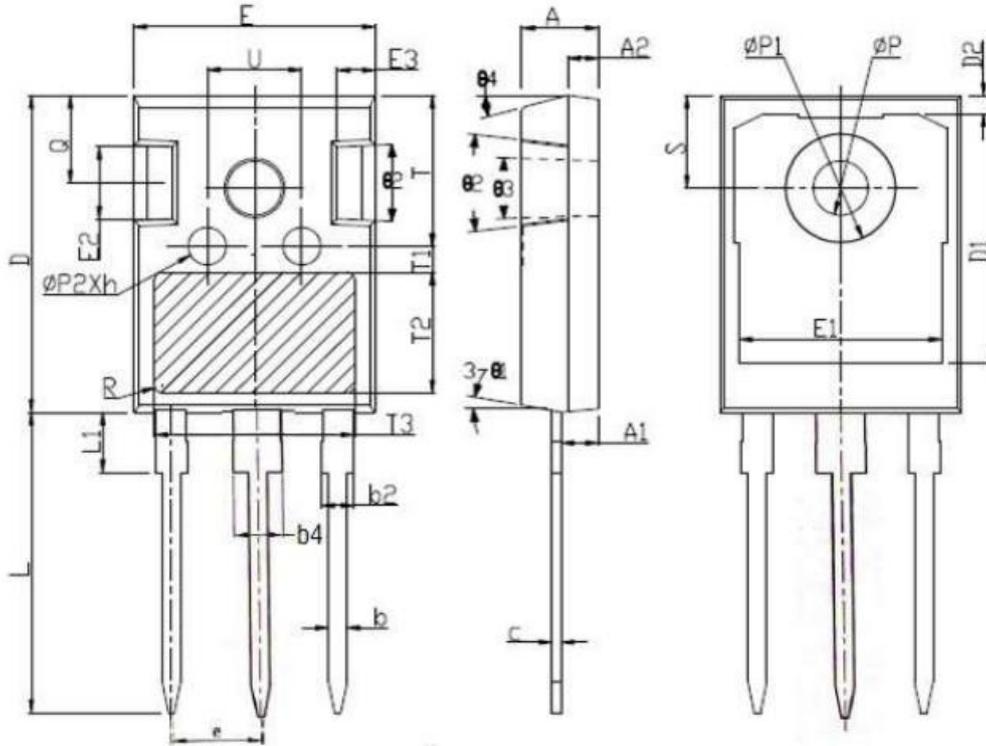


Fig 18. IGBT transient thermal resistance($D=tp/T$)

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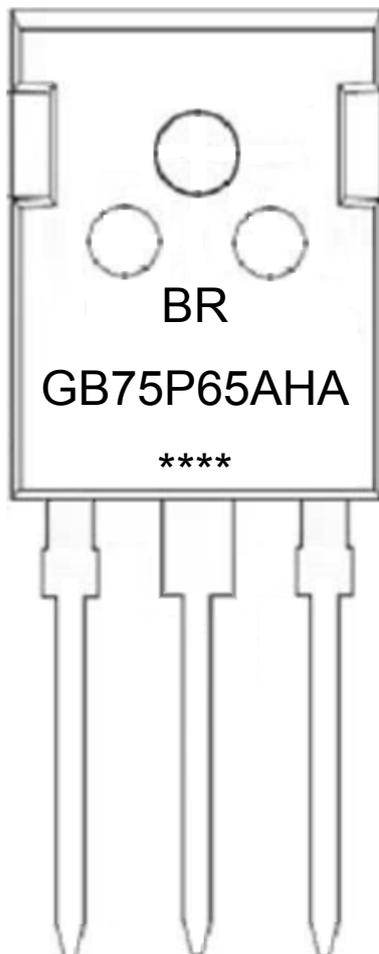
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外形尺寸图 / Package Dimensions



Symbol	Min	Nom	Max	Symbol	Min	Nom	Max
A	4.9	5.0	5.1	e	5.44BSC		
A1	2.3	2.4	2.5	h	0.05	0.10	0.15
A2	1.9	2.0	2.1	L	19.6	19.9	20.2
b	1.10	1.20	1.25	L1			4.3
b2	1.90	2.00	2.25	Φ p	3.5	3.6	3.75
b4	2.90	3.00	3.25	Φ p1			7.3
c	0.50	0.60	0.70	Φ p2	2.4	2.5	2.6
D	20.8	21.0	21.2	Q	5.3		5.9
D1	16.25	16.55	16.85	S	6.15BSC		
D2	1.05	1.20	1.35	T	9.8		10.2
E	15.6	15.8	16.0	T1	1.65REF		
E1	13.1	13.3	13.5	T2	8.0REF		
E2	4.9	5.0	5.1	T3	12.8REF		
E3	2.4	2.5	2.6	U	6.0		6.4
Unit		mm		type		T0-247G	

印章说明 / Marking Instructions



说明：

BR： 为公司代码

GB75P65AHA： 为型号代码

****： 为生产批号代码，随生产批号变化

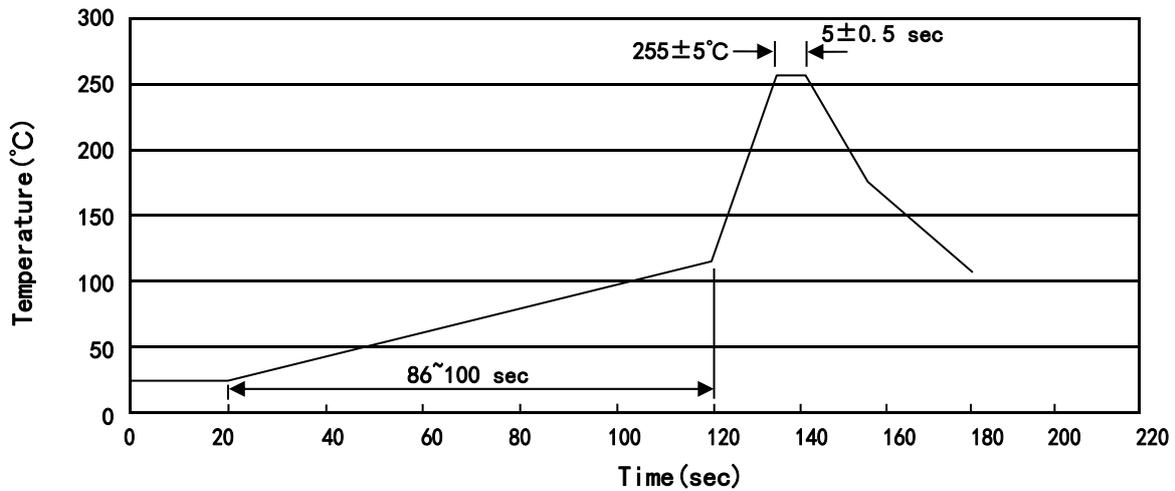
Note:

BR: Company Code

GB75P65AHA: Product Type Code

****: Lot No. Code, code change with Lot No

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-247	30	15	450	5	2250	520×44×6	580×158×55	595×300×178

使用说明 / Notices

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